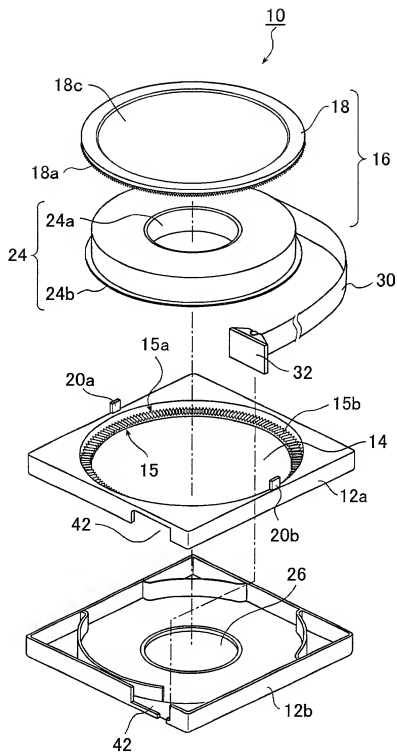


A cross-sectional view of a semiconductor device 10. The device features a substrate 12 with a top layer 15. A central region 16 contains a stack of layers 24a, 24b, 24c, and 24d. This central region is flanked by two side regions 18a and 18b. The side regions 18a and 18b are separated by a central barrier 18c. The top surface of the device is labeled 20a. The bottom surface of the device is labeled 26. The side walls of the device are labeled 15a and 15b. The top surface of the side regions 18a and 18b is labeled 22a. The bottom surface of the side regions 18a and 18b is labeled 30. The top surface of the central region 16 is labeled 24a.

FIG. 3



1005012.011802

FIG. 4

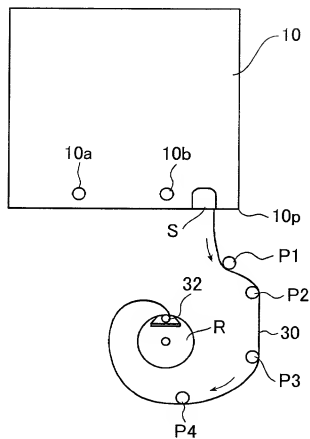
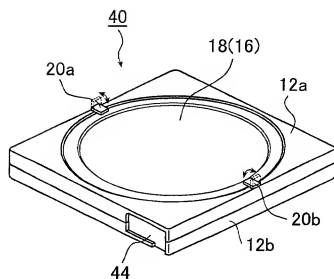


FIG. 5



1005012.01300

FIG. 6

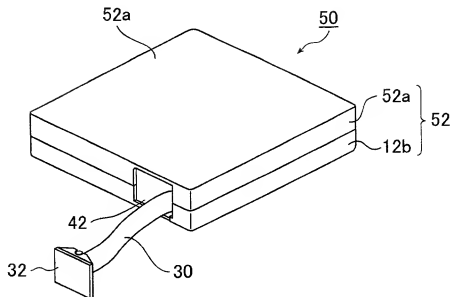
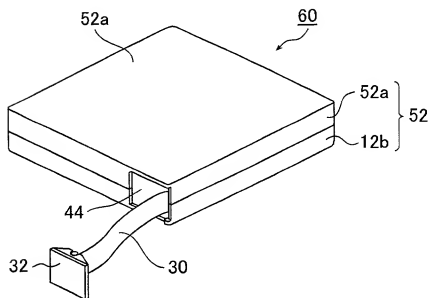
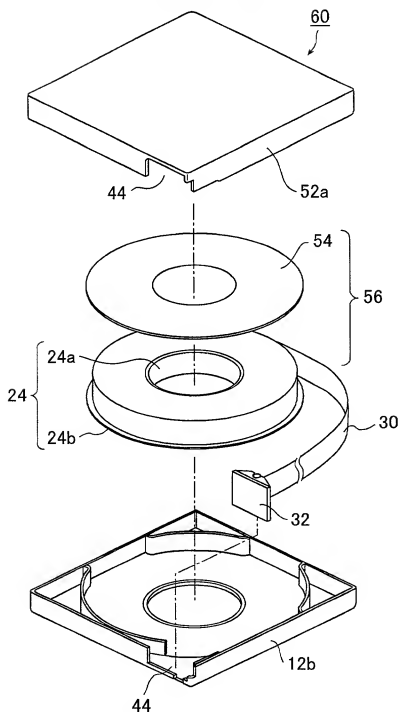


FIG. 7
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FIG. 8
PRIOR ART



1065012.01802